TOSHIBA Transistor Silicon NPN Epitaxial Type (Darlington power transistor)

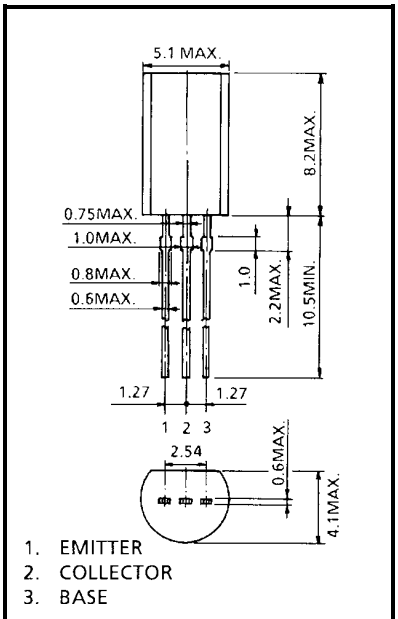
2SD2536

Switching Applications

Micro Motor Drive, Hammer Drive Applications

- High DC current gain: h_{FE} = 2000 (min) (V_{CE} = 2 V, I_C = 1 A)
- Low saturation voltage: $V_{CE\ (sat)}$ = 1.2 V (max)
  (I_C = 0.7 A, V_{BH} = 4.2 V)
- Zener diode included between collector and base.

Unit: mm



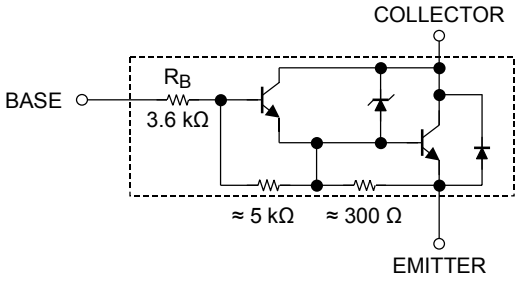
JEDEC	TO-92MOD
JEITA	—
TOSHIBA	2-5J1A

Weight: 0.36 g (typ.)

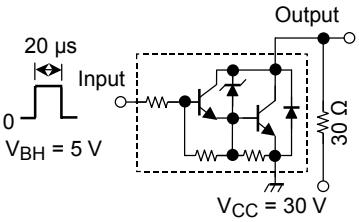
Maximum Ratings (Ta = 25°C)

Characteristics	Symbol	Rating	Unit
Collector-base voltage	V_{CBO}	85	V
Collector-emitter voltage	V_{CEO}	100 ± 15	V
Emitter-base voltage	V_{EBO}	6	V
Bias voltage	V_B	20	V
Collector current	I_C	2	A
Collector power dissipation	P_C	0.9	W
Base current	I_B	0.5	A
Junction temperature	T_j	150	°C
Storage temperature range	T_{stg}	−55 to 150	°C

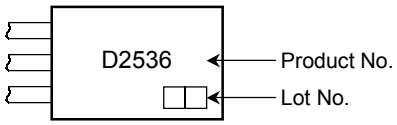
Equivalent Circuit



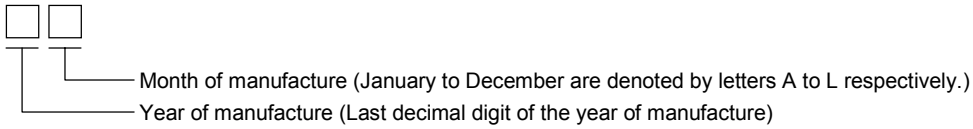
Electrical Characteristics (Ta = 25°C)

Characteristics		Symbol	Test Condition	Min	Typ.	Max	Unit
Collector cut-off current		I_{CBO}	V_{CB} = 80 V, I_E = 0	—	—	10	μA
Emitter cut-off current		I_{EBO}	V_{EB} = 6 V, I_C = 0	0.3	—	1.5	mA
Collector-emitter breakdown voltage		$V_{(BR)\ CEO}$	I_C = 10 mA, I_B = 0	85	100	115	V
Base resistance		R_B	—	2.5	3.6	4.7	kΩ
DC current gain		h_{FE}	V_{CE} = 2 V, I_C = 1 A	2000	—	—	
Collector-emitter saturation voltage		$V_{CE\ (sat)\ (1)}$	I_C = 0.7 A, V_{BH} = 4.2 V	—	—	1.2	V
		$V_{CE\ (sat)\ (2)}$	I_C = 1 A, V_{BH} = 4.2 V	—	—	1.5	
Input threshold voltage		V_{BL}	V_{CE} = 50 V, I_C = 100 μA	—	—	0.7	V
Collector output capacitance		C_{ob}	V_{CB} = 10 V, I_E = 0, f = 1 MHz	—	20	—	pF
Unclamped inductive load energy		$E_{S/B}$	L = 10 mH, I_C = 1 A, V_{BH} = 10 V	5	—	—	mJ
Switching time	Turn-on time	t_r	 Duty cycle ≤ 1%	—	0.3	—	μs
	Storage time	t_{stg}		—	4.0	—	
	Fall time	t_f		—	0.6	—	

Marking



Explanation of Lot No.



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